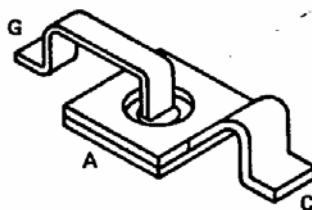


**S1210BM –
S1210MM SCR'S****12 A 200–600 V 10–25 mA**

The S1210 series silicon controlled rectifiers are high performance glass passivated PNP devices. These parts are intended for hybrid applications.

**MICRO MINI****Absolute Maximum Ratings** $T_A = 25^\circ\text{C}$ unless otherwise noted

Parameter	Part Nr.	Symbol	Min.	Max.	Unit	Test Conditions
Repetitive Peak Off State Voltage	S1210BM S1210DM S1210MM	V_{DRM} V_{RRM}	200 400 600		V V V	$T_J = -40^\circ\text{C}$ to 125°C $R_{GK} = 1\text{K}\Omega$
On-State Current		$I_{T(RMS)}$	12		A	All Conduction Angles $T_C = 85^\circ\text{C}$
Average On-State Current		$I_{T(AV)}$	7.6		A	Half Cycle, $\Theta = 180^\circ$, $T_C = 85^\circ\text{C}$
Nonrept. On-State Current		I_{TSM}	132		A	Half Cycle, 60 Hz
Nonrept. On-State Current		I_{TSM}	120		A	Half Cycle, 50 Hz
Fusing Current		I^2t	72		A^2s	$t = 10\text{ ms}$, Half Cycle
Peak Gate Current		I_{GM}	4		A	$10\mu\text{s}$ max.
Peak Gate Dissipation		P_{GM}	10		W	$10\mu\text{s}$ max.
Gate Dissipation		$P_{G(AV)}$	1		W	20 ms max.
Operating Temperature		T_J	-40	125	$^\circ\text{C}$	
Storage Temperature		T_{stg}	-40	150	$^\circ\text{C}$	
Case Temperature		T_C			$^\circ\text{C}$	Temperature measured on the substrate immediately adjacent to the Chip

Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

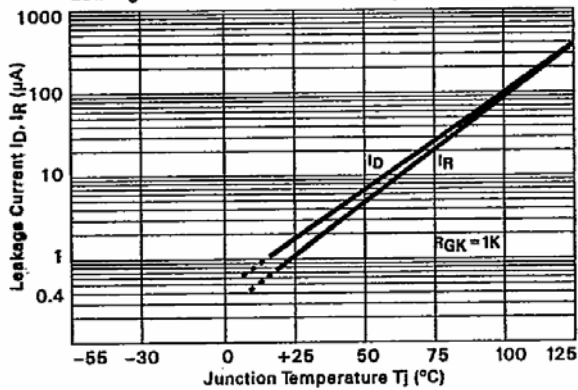
Parameter	Symbol	Min.	Max.	Unit	Test Conditions
Off-State Leakage Current	I_{DRM}/I_{RRM}		1.5	mA	@ $V_{DRM} + V_{RRM}$, $R_{GK} = 1\text{K}\Omega$, $T_J = 125^\circ\text{C}$
Off-State Leakage Current	I_{DRM}/I_{RRM}		5.0	μA	@ $V_{DRM} + V_{RRM}$, $R_{GK} = 1\text{K}\Omega$, $T_J = 25^\circ\text{C}$
On-State Voltage	V_T		1.80	V	at $I_T = 24\text{ A}$, $T_J = 25^\circ\text{C}$
On-State Threshold Voltage	$V_{T(TO)}$		1.0	V	$T_J = 125^\circ\text{C}$
On-State Slope Resistance	r_T		36	$\text{m}\Omega$	$T_J = 125^\circ\text{C}$
Gate Trigger Current	I_{GT}	10	25	mA	$V_D = 7\text{ V}$
Gate Trigger Voltage	V_{GT}		2.0	V	$V_D = 7\text{ V}$
Holding Current	I_H		38	mA	$R_{GK} = 1\text{K}\Omega$
Latching Current	I_L		75	mA	$R_{GK} = 1\text{K}\Omega$
Critical Rate of Voltage Rise	dv/dt	200		$\text{V}/\mu\text{s}$	$V_D = .67 \times V_{DRM}$, $R_{GK} = 1\text{K}\Omega$, $T_J = 125^\circ\text{C}$
Critical Rate of Current Rise	di/dt	100		$\text{A}/\mu\text{s}$	$I_G = 125\text{ mA}$, $di_G/dt = 1.25\text{ A}/\mu\text{s}$, $T_J = 125^\circ\text{C}$
Gate Controlled Delay Time	t_{gd}		500	ns	$I_G = 125\text{ mA}$, $di_G/dt = 1.25\text{ A}/\mu\text{s}$
Commutated Turn-Off Time	t_q		50	μs	$T_C = 85^\circ\text{C}$, $V_D = .67 \times V_{DRM}$, $V_R = 35\text{ V}$, $I_T = I_{T(AV)}$
Thermal Resistance junc. to case	$R_{\theta jc}$		1	K/W	50 micron solder on backside of Chip

Parts are 100% tested in Chip form with visual inspection after assembly.

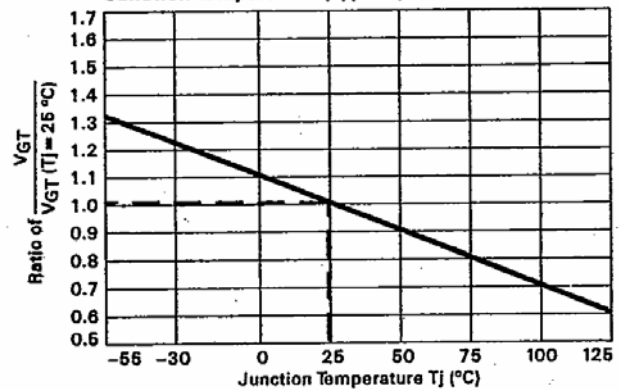
Per MIL-STD-105-D, parts will pass AQL 4.0 income inspection.

Typical Characteristics S12 - Chips

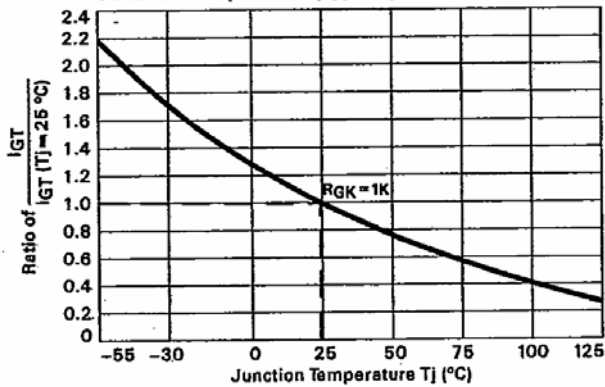
Leakage Current vs Junction Temperature (typical)



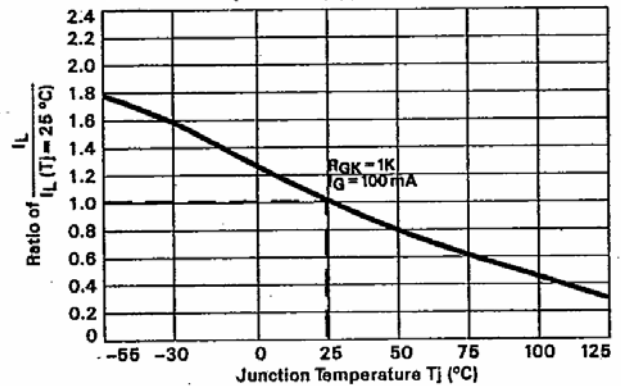
Normalized DC Gate Trigger Voltage vs Junction Temperature (typical)



Normalized DC Gate Trigger Current vs Junction Temperature (typical)



Normalized DC Latching Current vs Junction Temperature (typical)



Normalized DC Holding Current vs Junction Temperature (typical)

